

# RYC002N05

## 0.9V Drive Nch MOSFET

● **Structure**

Silicon N-channel MOSFET

● **Features**

- 1) High speed switing.
- 2) Small package(SST3).
- 3)Ultra low voltage drive(0.9V drive).

● **Application**

Switching

● **Packaging specifications**

Type	Package	Taping
	Code	T316
	Basic ordering unit (pieces)	3000
RYC002N05		○

● **Absolute maximum ratings (Ta = 25°C)**

Parameter	Symbol	Limits	Unit
Drain-source voltage	$V_{DSS}$	50	V
Gate-source voltage	$V_{GSS}$	±8	V
Drain current	Continuous	$I_D$	±200 mA
	Pulsed	$I_{DP}^{*1}$	±800 mA
Source current (Body Diode)	Continuous	$I_S$	150 mA
	Pulsed	$I_{SP}^{*1}$	800 mA
Power dissipation	$P_D^{*2}$	200	mW
Channel temperature	Tch	150	°C
Range of storage temperature	Tstg	-55 to +150	°C

\*1  $P_w \leq 10\mu s$ , Duty cycle  $\leq 1\%$

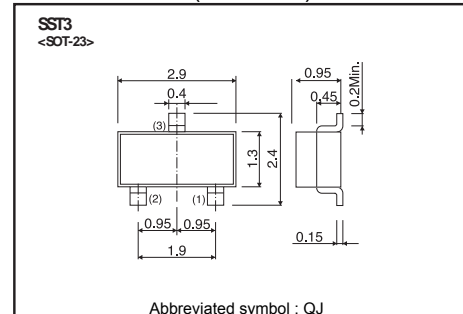
\*2 Each terminal mounted on a recommended land.

● **Thermal resistance**

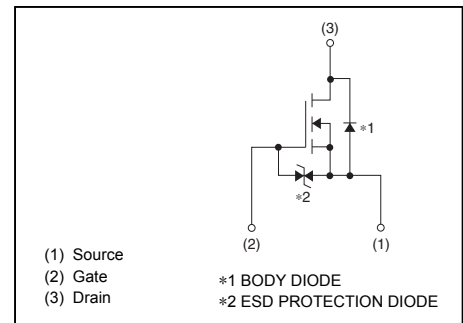
Parameter	Symbol	Limits	Unit
Channel to Ambient	$R_{th}(ch-a)^*$	625	°C / W

\* Each terminal mounted on a recommended land.

● **Dimensions (Unit : mm)**



● **Inner circuit**



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**● Electrical characteristics (Ta = 25°C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	-	-	±10	μA	$V_{GS}=\pm 8V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	50	-	-	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	μA	$V_{DS}=50V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	0.3	-	0.8	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	1.6	2.2	Ω	$I_D=200mA, V_{GS}=4.5V$
		-	1.7	2.4		$I_D=200mA, V_{GS}=2.5V$
		-	2.0	2.8		$I_D=200mA, V_{GS}=1.5V$
		-	2.2	3.3		$I_D=100mA, V_{GS}=1.2V$
		-	3.0	9.0		$I_D=10mA, V_{GS}=0.9V$
Forward transfer admittance	$ Y_{fs} ^*$	0.2	-	-	S	$I_D=200mA, V_{DS}=10V$
Input capacitance	$C_{iss}$	-	26	-	pF	$V_{DS}=10V$
Output capacitance	$C_{oss}$	-	6	-	pF	$V_{GS}=0V$
Reverse transfer capacitance	$C_{rss}$	-	3	-	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	5	-	ns	$I_D=100mA, V_{DD}=25V$
Rise time	$t_r^*$	-	8	-	ns	$V_{GS}=4.5V$
Turn-off delay time	$t_{d(off)}^*$	-	17	-	ns	$R_L=250\Omega$
Fall time	$t_f^*$	-	43	-	ns	$R_G=10\Omega$

\*Pulsed

**● Body diode characteristics (Source-Drain) (Ta = 25°C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	$V_{SD}^*$	-	-	1.2	V	$I_S=200mA, V_{GS}=0V$

\*Pulsed